L Number	Hits	Search Text	DB	Time stamp
1	50	corning adj glass adj "7059"	USPAT	2003/06/12 11:18
2	1	us-5622814-\$.did. and (al aluminum)	USPAT	2003/06/12 11:38
3	9110	active adj matrix	USPAT	2003/06/12 11:40
4	39	(active adj matrix) with repeat\$3	USPAT	2003/06/12 11:47
5	6356	microelectromechanical adj system adj	USPAT;	2003/06/12 11:40
3	0330	device mems!	US-PGPUB;	2003/00/12 11:40
		device mems:	EPO; JPO;	
			DERWENT	
6	27721	active adj matrix	USPAT;	2003/06/12 11:40
6	21121	active adj matrix	US-PGPUB;	2003/00/12 11:40
			EPO; JPO;	
			DERWENT	
7	10	(microelectromechanical adj system adj	USPAT;	2003/06/12 11:40
7	10	device mems! ) with (active adj matrix)	US-PGPUB;	2003/00/12 11.40
		device mems: / with (active ad) matrix/	EPO; JPO;	
			DERWENT	
_	2	(/astima adi matrim) with report(2) and	USPAT	2003/06/12 11:47
8	2	((active adj matrix) with repeat\$3) and 430/\$.ccls.	USPAI	2003/06/12 11:47
	4100		TICDAM.	2003/06/12 11:48
9	4100	(semiconductor) with repeat\$3	USPAT	
10	369	((semiconductor) with repeat\$3) and	USPAT	2003/06/12 11:48
11	0011	430/\$.ccls.	IIGD A M	2003/06/12 11:50
11	2011	(semiconductor) with repeat\$3 with (step	USPAT	2003/06/12 11:30
1.0	005	method process)	HCDAM	3003/05/13 11:50
12	225	((semiconductor) with repeat\$3 with (step	USPAT	2003/06/12 11:50
1.4	005	method process)) and 430/\$.ccls.	II CD A M	2003/06/12 11:51
14	225	(((semiconductor) with repeat\$3 with (step	USPAT	2003/06/12 11:51
		method process)) and 430/\$.ccls.) and		
1.5	00	430/\$.ccls.	TIGDE III	2002/06/10 11:51
15	22	((semiconductor) with repeat\$3 with (step	USPAT	2003/06/12 11:51
		method process) with (known typical\$3		
1.0	0000	conventional\$3)) and 430/\$.ccls.	IIGDD III	2002/06/12 12:26
16	2909	(backside back-side back adj side) near2	USPAT;	2003/06/12 12:26
		(expos\$4 irradiat\$5)	US-PGPUB;	
			EPO; JPO;	
1.7	1	//	DERWENT	2002/06/12 11-55
17	1	((semiconductor) with repeat\$3 with (step	USPAT;	2003/06/12 11:55
		method process)) same ((backside back-side	US-PGPUB;	
		back adj side) near2 (expos\$4 irradiat\$5)	EPO; JPO;	
1.0	1.5		DERWENT	2003/06/12 11:55
18	15		USPAT;	2003/06/12 11:55
		method process)) and ((backside back-side	US-PGPUB;	
		back adj side) near2 (expos\$4 irradiat\$5)	EPO; JPO;	
10	0	/	DERWENT USPAT	2002/06/12 11.57
19	0	(semiconductor) with repeat\$3 with (step	USPAT	2003/06/12 11:57
		method process) with (known typical\$3		
		conventional\$3) with (many multiple) with		
20	2	layer	Henam	2002/06/12 11:57
20	3	(semiconductor) with repeat\$3 with (step	USPAT	2003/06/12 11:57
		method process) with (known typical\$3		]
12	100	conventional\$3) with (many multiple)	HODE	2002/05/12 11 50
13	130	(semiconductor) with repeat\$3 with (step	USPAT	2003/06/12 11:59
		method process) with (known typical\$3		
	25	conventional\$3)	HODAG	2002/06/12 12 12
21	85	, · · · · · · · · · · · · · · · · · · ·	USPAT	2003/06/12 12:10
		method process) with (known typical\$3		
	^	conventional\$3)	IIODam	2002/06/10 10 11
22	2	(semiconductor) with repeat\$3 with (steps!	USPAT	2003/06/12 12:11
		method process) with (required) with		
,,	^	(multiple near2 layer)	IICD*M	2002/06/12 12 12
23	0	(electrodes) with repeat\$3 with (steps!	USPAT	2003/06/12 12:12
		method process) with (required) with		
	1700	(multiple near2 layer)	II.C.D.a.m	2002/06/12 12 12
24	1789	(electrodes) with repeat\$3 with (steps!	USPAT	2003/06/12 12:13
۱ ا		method process)	HODAT	2002/06/20 20 20
25	58	(electrodes) with repeat\$3 with (steps!	USPAT	2003/06/12 12:18
		method process) with (known conventional\$2		
26	222	typical\$2)		0000/00/10 55 55
		(pattern) with repeat\$3 with (steps!	USPAT	2003/06/12 12:18
26	323		1	
26	323	<pre>method process) with (known conventional\$2 typical\$2)</pre>		

27	81	(438/\$.ccls. 430/\$.ccls.) and ((pattern) with repeat\$3 with (steps! method process) with (known conventional\$2 typical\$2))	USPAT	2003/06/12 12:19
28	11941	(back) near2 (expos\$4 irradiat\$5)	USPAT; US-PGPUB; EPO; JPO;	2003/06/12 12:26
29	10292	((back) near2 (expos\$4 irradiat\$5) ) not ((backside back-side back adj side) near2 (expos\$4 irradiat\$5) )	DERWENT USPAT; US-PGPUB; EPO; JPO;	2003/06/12 12:27
30	151	(((back) near2 (expos\$4 irradiat\$5) ) not ((backside back-side back adj side) near2 (expos\$4 irradiat\$5) )) same repeat\$3	DERWENT USPAT; US-PGPUB; EPO; JPO;	2003/06/12 12:28
31	63	((backside back-side back adj side) near2 (expos\$4 irradiat\$5) )) same (repeat\$3	DERWENT USPAT; US-PGPUB; EPO; JPO;	2003/06/12 12:32
32	2	with (steps method process)) ("5707785").PN.	DERWENT USPAT; US-PGPUB; EPO; JPO;	2003/06/12 12:32
-	26	MILES-MARKin. MILES-MARK-Win. MILES-M-Win.	DERWENT USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/06/11 16:34
-	2907	(backside back-side back adj side) near2 (expos\$4 irradiat\$5)	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2003/06/12 11:52
_	398591	resist photoresist photo-resist	DERWENT USPAT; US-PGPUB; EPO; JPO;	2003/06/11 16:38
_	311632	photosensitive photo-sensitive (sensitive near (photo light energy radiation))	DERWENT USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/11 16:39
	357428	uv ultraviolet ultra-violet ultra adj violet	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/11 16:40
_	32060	<pre>((resist photoresist photo-resist) (photosensitive photo-sensitive (sensitive near (photo light energy radiation)))) with negative</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/11 16:46
_	24		USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/11 17:32
_	2		USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/11 17:34
_	6323	microelectromechanical adj system adj device mems!	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/12 11:40
_	34	<pre>(microelectromechanical adj system adj device mems!) and ((backside back-side back adj side) near2 (expos\$4 irradiat\$5))</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/11 18:04

_	7	<pre>(microelectromechanical adj system adj device mems!) and ((backside back-side back adj side) near2 (expos\$4 irradiat\$5)) and (((resist photoresist photo-resist) (photosensitive photo-sensitive (sensitive near (photo light energy radiation))))</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/11 17:44
-	28	with negative) (ni nickel al aluminum) same ((backside back-side back adj side) near2 (expos\$4 irradiat\$5)) same ((resist photoresist photo-resist) (photosensitive photo-sensitive (sensitive near (photo light energy radiation))) (((resist photoresist photo-resist) (photosensitive photo-sensitive (sensitive near (photo-sensitive (sensitive near (photo-sensitive photo-sensitive near (photo-sensitive near (photo-sensi	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/11 17:52
-	177	light energy radiation)))) with negative)) ((backside back-side back adj side) near2 (expos\$4 irradiat\$5)) same (groove strip stripe transvers\$4 longitudinal\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/11 17:57
-	4	<pre>(((backside back-side back adj side) near2 (expos\$4 irradiat\$5)) same (groove strip stripe transvers\$4 longitudinal\$4)) same (((resist photoresist photo-resist) (photosensitive photo-sensitive (sensitive near (photo light energy radiation)))) with negative)</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/11 17:55
_	17	(((backside back-side back adj side) near2 (expos\$4 irradiat\$5)) same (groove strip stripe transvers\$4 longitudinal\$4)) same ((resist photoresist photo-resist) (photosensitive photo-sensitive (sensitive near (photo light energy radiation)))) not (((backside back-side back adj side) near2 (expos\$4 irradiat\$5)) same (groove strip stripe transvers\$4 longitudinal\$4)) same (((resist photoresist photo-resist) (photosensitive photo-sensitive (sensitive near (photo light energy radiation)))) with negative))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/11 17:55
_	50	((backside back-side back adj side) near2 (expos\$4 irradiat\$5)) same (transvers\$4 longitudinal\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/11 17:58
-	6	<pre>(((backside back-side back adj side) near2 (expos\$4 irradiat\$5)) same (transvers\$4 longitudinal\$4)) and ((resist photoresist photo-resist) (photosensitive photo-sensitive (sensitive near (photo light energy radiation))) 430/\$.CCLS.)</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/11 18:01
-	2	((backside back-side back adj side) near2 (expos\$4 irradiat\$5)) SAME (microelectromechanical adj system adj device mems!)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/11 18:01
-	1003	((backside back-side back adj side) near2 (expos\$4 irradiat\$5)) with ((resist photoresist photo-resist) (photosensitive photo-sensitive (sensitive near (photo light energy radiation))) (uv ultraviolet ultra-violet ultra adj violet) laser mask photomask light)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/11 18:07
-	584	((backside back-side back adj side) near2 (expos\$4 irradiat\$5)) with ((resist photoresist photo-resist) (photosensitive photo-sensitive (sensitive near (photo light energy radiation))) (uv ultraviolet ultra-violet ultra adj violet) (((resist photoresist photo-resist) (photosensitive photo-sensitive (sensitive near (photo light energy radiation)))) with negative) mask photomask)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/11 18:11

	110		TTODAM.	2002/06/11 10:12
-	410	((backside back-side back adj side) near2	USPAT;	2003/06/11 18:12
1		(expos\$4 irradiat\$5)) with ((resist	US-PGPUB	
		photoresist photo-resist) (photosensitive		j
	İ	photo-sensitive (sensitive near (photo		
		light energy radiation))) (uv ultraviolet		l
		ultra-violet ultra adj violet) (((resist		
		photoresist photo-resist) (photosensitive		
		photo-sensitive (sensitive near (photo		
1		light energy radiation)))) with negative)		
		mask photomask)		
-	58	(((backside back-side back adj side) near2	USPAT;	2003/06/11 18:59
		(expos\$4 irradiat\$5)) with ((resist	US-PGPUB	
		photoresist photo-resist) (photosensitive		
		photo-sensitive (sensitive near (photo		
		light energy radiation))) (uv ultraviolet		
		ultra-violet ultra adj violet) mask		
		photomask)) same negative		
-	1	us-6304309-\$.did. and (orthogonal\$3	USPAT;	2003/06/11 19:01
	1	transvers\$5)	US-PGPUB	
-	324	((backside back-side back adj side) near2	USPAT;	2003/06/11 19:01
		(expos\$4 irradiat\$5)) and (orthogonal\$3	US-PGPUB;	
		transvers\$5)	EPO; JPO;	
į	ĺ		DERWENT	ĺ
_	18	((backside back-side back adj side) near2	USPAT;	2003/06/11 19:03
		(expos\$4 irradiat\$5)) same (orthogonal\$3	US-PGPUB;	
		transvers\$5)	EPO; JPO;	
			DERWENT	
_	23	(((backside back-side back adj side) near2	USPAT;	2003/06/12 11:16
		(expos\$4 irradiat\$5)) same ((resist	US-PGPUB;	
		photoresist photo-resist) (photosensitive	EPO; JPO;	
		photo-sensitive (sensitive near (photo	DERWENT	
		light energy radiation))))) and (layer		
		same (orthogonal\$3 transvers\$5))		